December 2014

4N38M, H11D1M, H11D3M, MOC8204M
6-Pin DIP High Voltage Phototransistor Optocouplers

Features

- High Voltage:
  - MOC8204M, BV_{CEO} = 400 V
  - H11D1M, BV_{CEO} = 300 V
  - H11D3M, BV_{CEO} = 200 V
- Safety and Regulatory Approvals:
  - UL1577, 4,170 VAC_{RMS} for 1 Minute
- DIN-EN/IEC60747-5-5, 850 V Peak Working Insulation Voltage

Applications

- Power Supply Regulators
- Digital Logic Inputs
- Microprocessor Inputs
- Appliance Sensor Systems
- Industrial Controls

Description

The 4N38M, H11D1M, H11D3M, and MOC8204M are phototransistor-type optically coupled optoisolators. A gallium arsenide infrared emitting diode is coupled with a high voltage NPN silicon phototransistor. The device is supplied in a standard plastic six-pin dual-in-line package.

Schematic

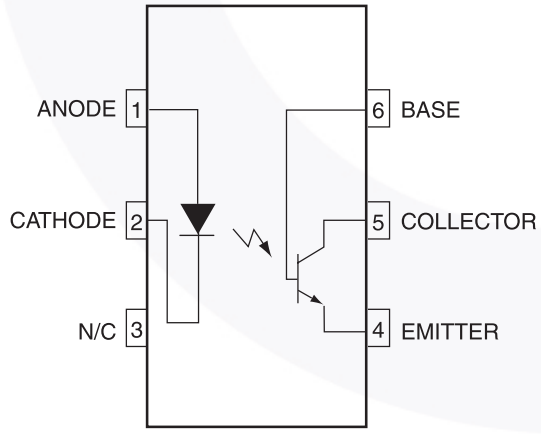

Figure 1. Schematic

Package Outlines

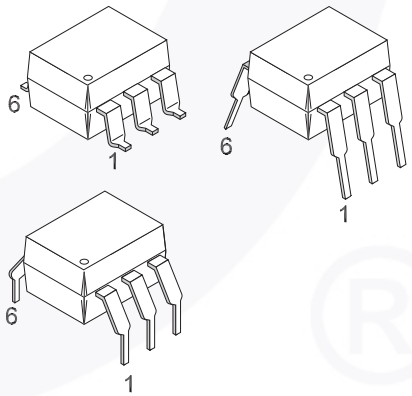

Figure 2. Package Outlines